



Thyristor

$$V_{RRM} = 1200\text{ V}$$

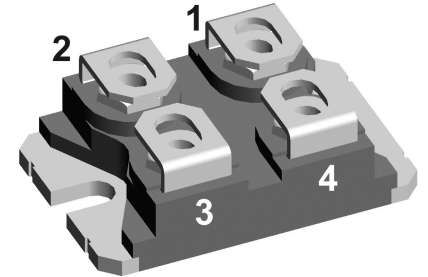
$$I_{TAV} = 40\text{ A}$$

$$V_T = 1.29\text{ V}$$

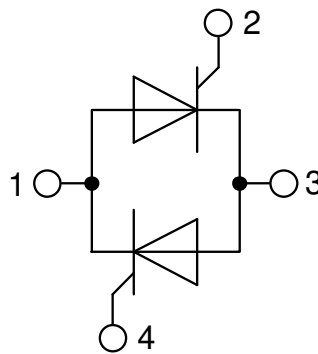
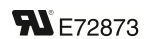
AC Controlling
1~ full-controlled

Part number

MMO74-12io6



Backside: isolated



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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| Thyristor | | | Ratings | | | |
|----------------|--|---|---------------------------|------|------|-------------------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| $V_{RSM/DSM}$ | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1300 | V |
| $V_{RRM/DRM}$ | max. repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1200 | V |
| I_{RD} | reverse current, drain current | $V_{R/D} = 1200 V$ | $T_{VJ} = 25^{\circ}C$ | | 100 | μA |
| | | $V_{R/D} = 1200 V$ | $T_{VJ} = 125^{\circ}C$ | | 6 | mA |
| V_T | forward voltage drop | $I_T = 40 A$ | $T_{VJ} = 25^{\circ}C$ | | 1.29 | V |
| | | $I_T = 80 A$ | | | 1.61 | V |
| | | $I_T = 40 A$ | $T_{VJ} = 125^{\circ}C$ | | 1.29 | V |
| | | $I_T = 80 A$ | | | 1.70 | V |
| I_{TAV} | average forward current | $T_C = 95^{\circ}C$ | $T_{VJ} = 150^{\circ}C$ | | 40 | A |
| I_{RMS} | RMS forward current per phase | 180° sine | | | 88 | A |
| V_{T0} | threshold voltage | } for power loss calculation only | $T_{VJ} = 150^{\circ}C$ | | 0.87 | V |
| r_T | slope resistance | | | | 10.5 | m Ω |
| R_{thJC} | thermal resistance junction to case | | | | 0.7 | K/W |
| R_{thCH} | thermal resistance case to heatsink | | | 0.1 | | K/W |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}C$ | | 180 | W |
| I_{TSM} | max. forward surge current | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}C$ | | 600 | A |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 650 | A |
| | | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 150^{\circ}C$ | | 510 | A |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 550 | A |
| I^2t | value for fusing | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}C$ | | 1.80 | kA ² s |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 1.76 | kA ² s |
| | | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 150^{\circ}C$ | | 1.30 | kA ² s |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 1.26 | kA ² s |
| C_J | junction capacitance | $V_R = 400 V \quad f = 1 \text{ MHz}$ | $T_{VJ} = 25^{\circ}C$ | | 22 | pF |
| P_{GM} | max. gate power dissipation | $t_p = 30 \mu s$ | $T_C = 150^{\circ}C$ | | 10 | W |
| | | $t_p = 300 \mu s$ | | | 5 | W |
| P_{GAV} | average gate power dissipation | | | | 0.5 | W |
| $(di/dt)_{cr}$ | critical rate of rise of current | $T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$ | repetitive, $I_T = 120 A$ | | 100 | A/ μs |
| | | $t_p = 200 \mu s; di_G/dt = 0.3 A/\mu s;$ $I_G = 0.3 A; V = \frac{2}{3} V_{DRM}$ | non-repet., $I_T = 40 A$ | | 500 | A/ μs |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage | $V = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 150^{\circ}C$ | | 1000 | V/ μs |
| | | $R_{GK} = \infty$; method 1 (linear voltage rise) | | | | |
| V_{GT} | gate trigger voltage | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 1.5 | V |
| | | | $T_{VJ} = -40^{\circ}C$ | | 1.6 | V |
| I_{GT} | gate trigger current | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 100 | mA |
| | | | $T_{VJ} = -40^{\circ}C$ | | 150 | mA |
| V_{GD} | gate non-trigger voltage | $V_D = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 150^{\circ}C$ | | 0.2 | V |
| I_{GD} | gate non-trigger current | | | | 5 | mA |
| I_L | latching current | $t_p = 10 \mu s$ | $T_{VJ} = 25^{\circ}C$ | | 450 | mA |
| | | $I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$ | | | | |
| I_H | holding current | $V_D = 6 V \quad R_{GK} = \infty$ | $T_{VJ} = 25^{\circ}C$ | | 100 | mA |
| t_{gd} | gate controlled delay time | $V_D = \frac{1}{2} V_{DRM}$ | $T_{VJ} = 25^{\circ}C$ | | 2 | μs |
| | | $I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$ | | | | |
| t_q | turn-off time | $V_R = 100 V; I_T = 20 A; V = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s \quad dv/dt = 15 V/\mu s \quad t_p = 200 \mu s$ | $T_{VJ} = 125^{\circ}C$ | | 150 | μs |



| Package SOT-227B (minibloc) | | | | Ratings | | | |
|-----------------------------|--|----------------------|-------------------------------------|---------|------|------|--|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit | |
| I_{RMS} | RMS current | per terminal | | | 150 | A | |
| T_{VJ} | virtual junction temperature | | -40 | | 150 | °C | |
| T_{op} | operation temperature | | -40 | | 125 | °C | |
| T_{stg} | storage temperature | | -40 | | 150 | °C | |
| Weight | | | | 30 | | g | |
| M_D | mounting torque | | 1.1 | | 1.5 | Nm | |
| M_T | terminal torque | | 1.1 | | 1.5 | Nm | |
| $d_{Spp/App}$ | creepage distance on surface striking distance through air | terminal to terminal | 10.5 | 3.2 | | mm | |
| $d_{Spb/Apb}$ | | terminal to backside | 8.6 | 6.8 | | mm | |
| V_{ISOL} | isolation voltage | t = 1 second | | | 3000 | V | |
| | | t = 1 minute | 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA | | 2500 | V | |

Product Marking



| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MMO74-12io6 | MMO74-12io6 | Tube | 10 | 459380 |

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

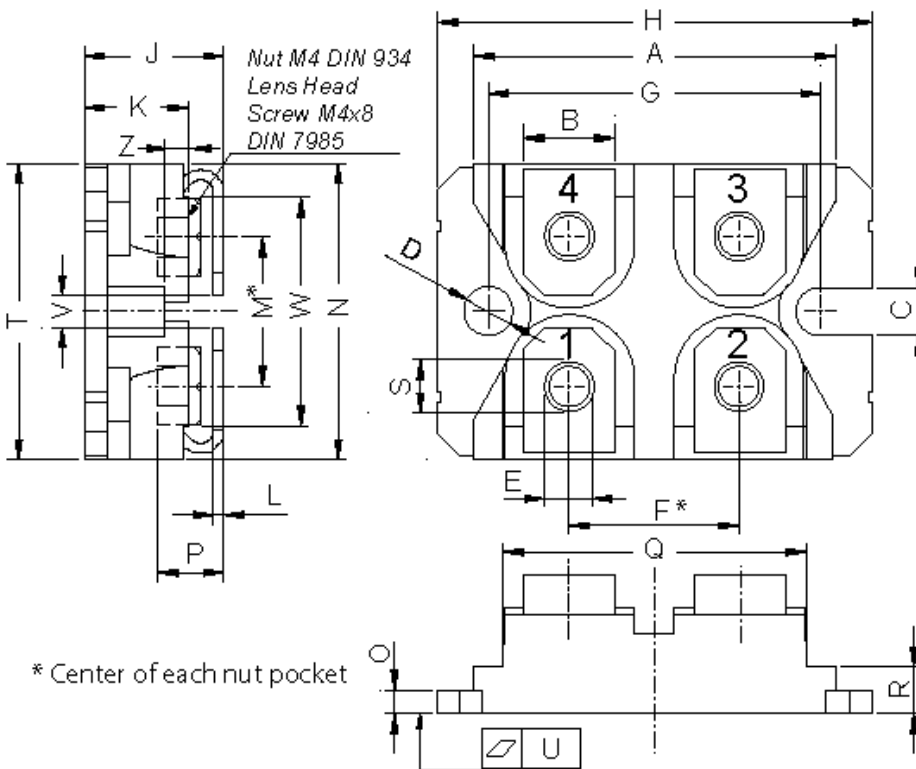


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| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 0.87 | V |
| $R_{0\ max}$ | slope resistance * | 9.7 | mΩ |



Outlines SOT-227B (minibloc)



| Dim. | Millimeter | | Inches | |
|------|------------|-------|--------|-------|
| | min | max | min | max |
| A | 31.50 | 31.88 | 1.240 | 1.255 |
| B | 7.80 | 8.20 | 0.307 | 0.323 |
| C | 4.09 | 4.29 | 0.161 | 0.169 |
| D | 4.09 | 4.29 | 0.161 | 0.169 |
| E | 4.09 | 4.29 | 0.161 | 0.169 |
| F | 14.91 | 15.11 | 0.587 | 0.595 |
| G | 30.12 | 30.30 | 1.186 | 1.193 |
| H | 37.80 | 38.23 | 1.488 | 1.505 |
| J | 11.68 | 12.22 | 0.460 | 0.481 |
| K | 8.92 | 9.60 | 0.351 | 0.378 |
| L | 0.74 | 0.84 | 0.029 | 0.033 |
| M | 12.50 | 13.10 | 0.492 | 0.516 |
| N | 25.15 | 25.42 | 0.990 | 1.001 |
| O | 1.95 | 2.13 | 0.077 | 0.084 |
| P | 4.95 | 6.20 | 0.195 | 0.244 |
| Q | 26.54 | 26.90 | 1.045 | 1.059 |
| R | 3.94 | 4.42 | 0.155 | 0.167 |
| S | 4.55 | 4.85 | 0.179 | 0.191 |
| T | 24.59 | 25.25 | 0.968 | 0.994 |
| U | -0.05 | 0.10 | -0.002 | 0.004 |
| V | 3.20 | 5.50 | 0.126 | 0.217 |
| W | 19.81 | 21.08 | 0.780 | 0.830 |
| Z | 2.50 | 2.70 | 0.098 | 0.106 |



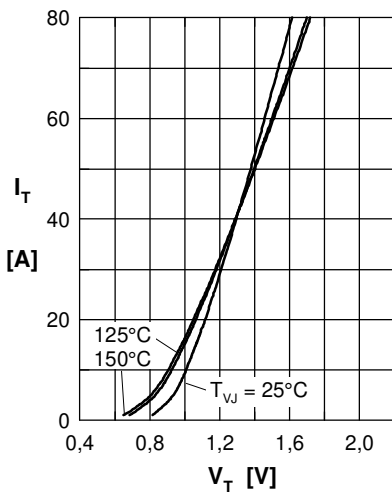
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Fig. 1 Forward characteristics

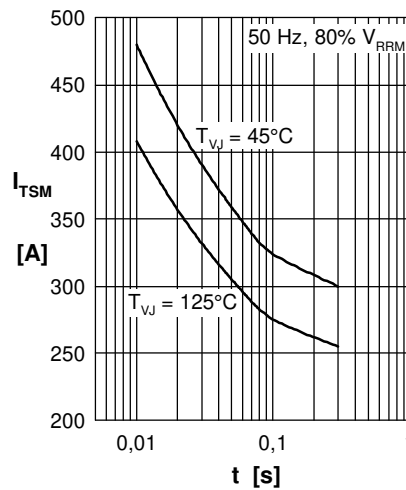


Fig. 2 Surge overload current

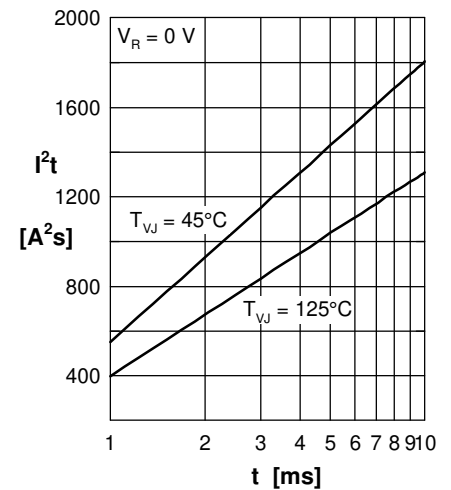
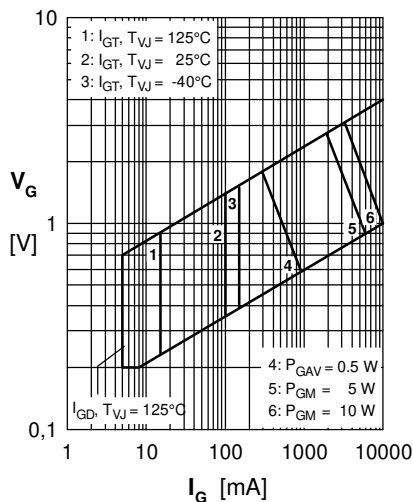

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics

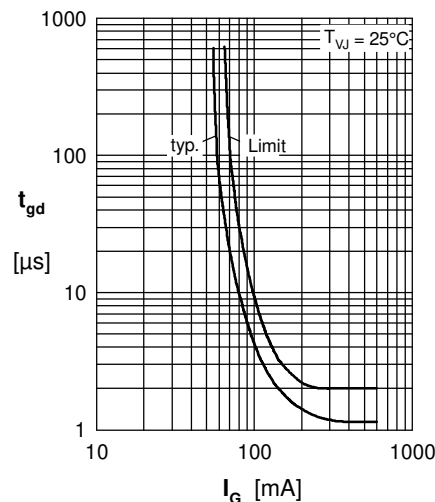


Fig. 5 Gate controlled delay time

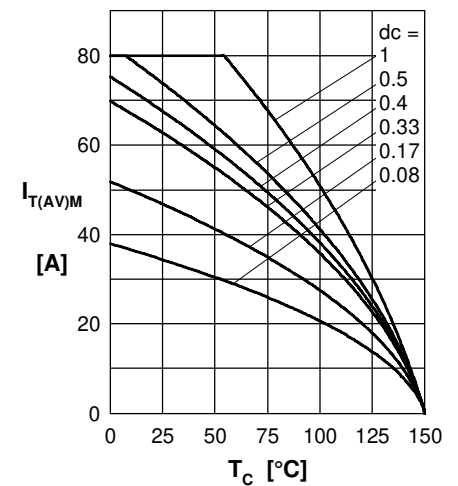


Fig. 6 Max. forward current at case temperature

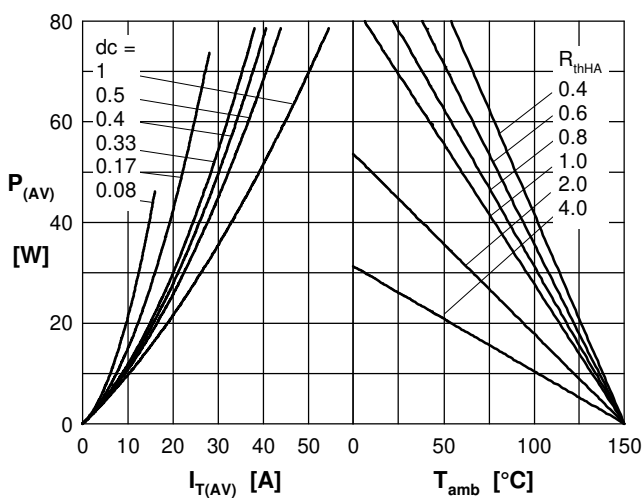
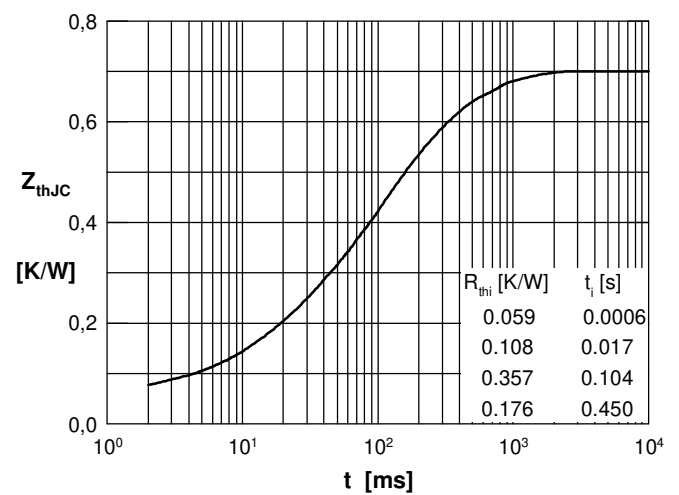

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case